

SANYO	No.1200C	2SA1290/2SC3254
	PNP/NPN Epitaxial Planar Silicon Transistors	
60V/7A High-Speed Switching Applications		

Applications

- Various inductance lamp drivers for electrical equipment.
- Inverters, converters (strobo, flash, fluorescent lamp lighting circuit).
- Power amp (high power car stereo, motor controller).
- High-speed switching (switching regulator, driver).

Features

- Low saturation voltage.
- Excellent current dependence of h_{FE} .
- Short switching time.

() : 2SA1290

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	(-)	80 V
Collector-to-Emitter Voltage	V_{CE0}	(-)	60 V
Emitter-to-Base Voltage	V_{EB0}	(-)	5 V
Collector Current	I_C	(-)	7 A
Collector Current (Pulse)	I_{CP}	(-)	10 A
Collector Dissipation	P_C	$T_c = 25^\circ\text{C}$	35 W
Junction Temperature	T_j		150 $^\circ\text{C}$
Storage Temperature	T_{stg}		- 55 to + 150 $^\circ\text{C}$

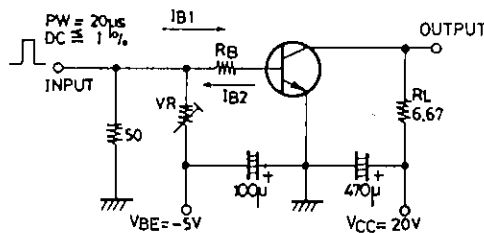
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)40\text{V}, I_E = 0$			(-)	0.1 mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{V}, I_C = 0$			(-)	0.1 mA
DC Current Gain	h_{FE}	$V_{CE} = (-)2\text{V}, I_C = (-)1\text{A}$	70*		280*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)5\text{V}, I_C = (-)1\text{A}$		100		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)3.5\text{A}, I_B = (-)0.175\text{A}$			(-)	0.4 V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1\text{mA}, I_E = 0$	(-)		80	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	(-)		60	V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1\text{mA}, I_C = 0$	(-)		5	V
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μs
Storage Time	t_{stg}	"		0.5		μs
Fall Time	t_f	"		0.1		μs

* : The 2SA1290/2SC3254 are classified by 1A h_{FE} as follows

70	Q	140	100	R	200	140	S	280
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Switching Time Test Circuit

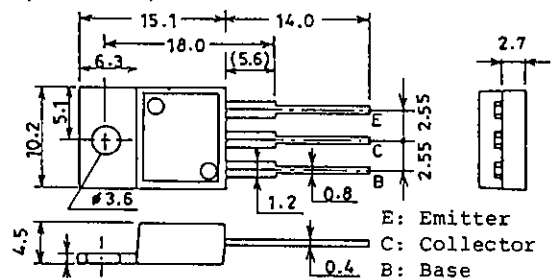


(For PNP, the polarity is reversed). $20I_{B1} = -20I_{B2} = I_C = 3\text{A}$

Unit (resistance: Ω , capacitance: F)

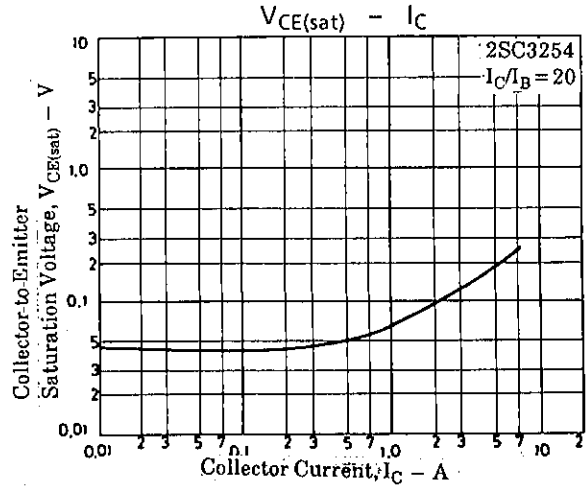
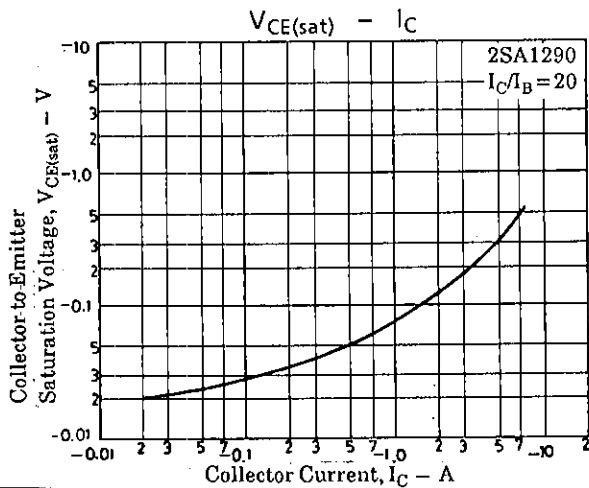
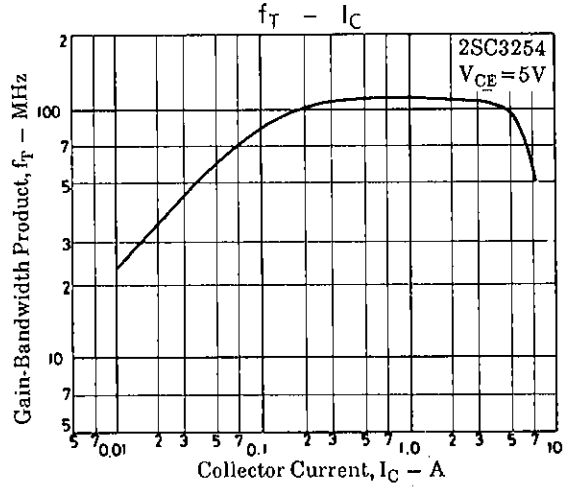
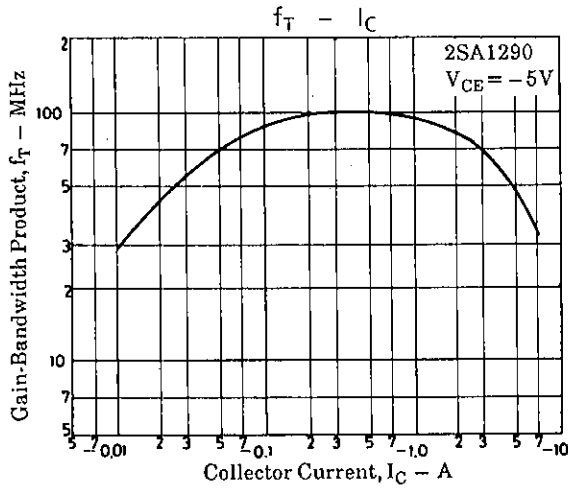
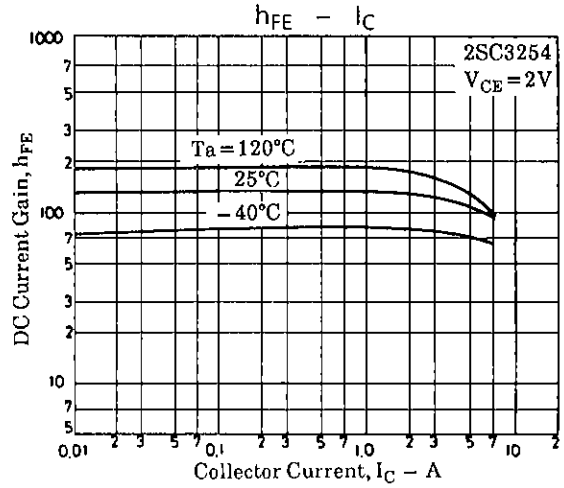
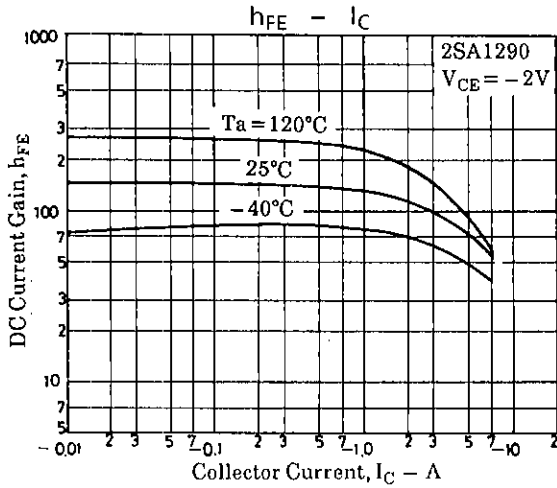
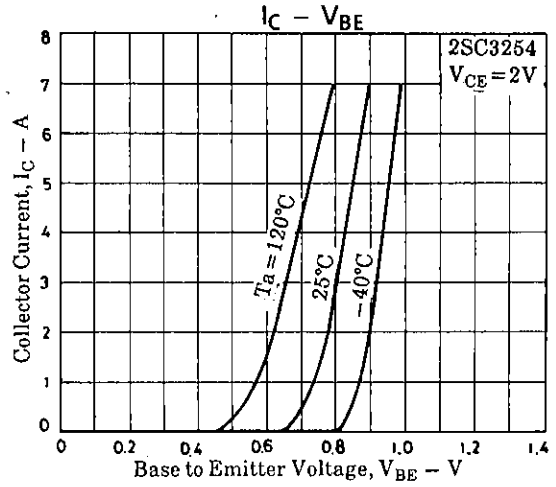
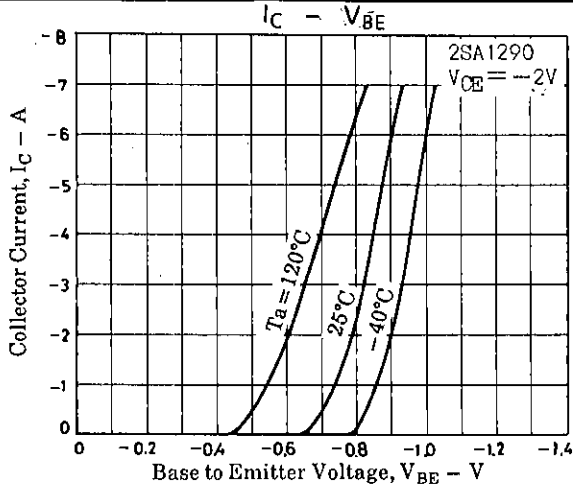
Package Dimensions 2010B

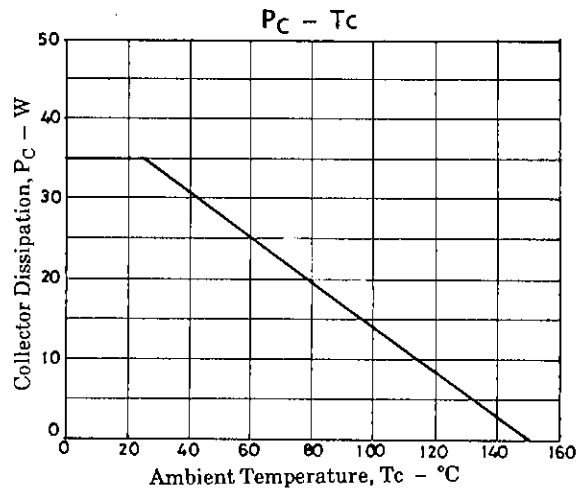
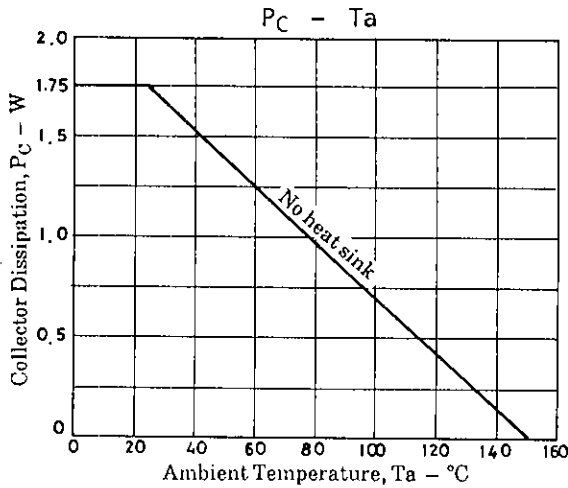
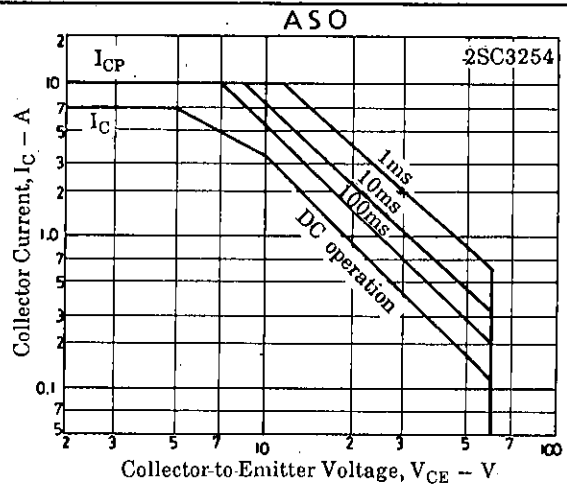
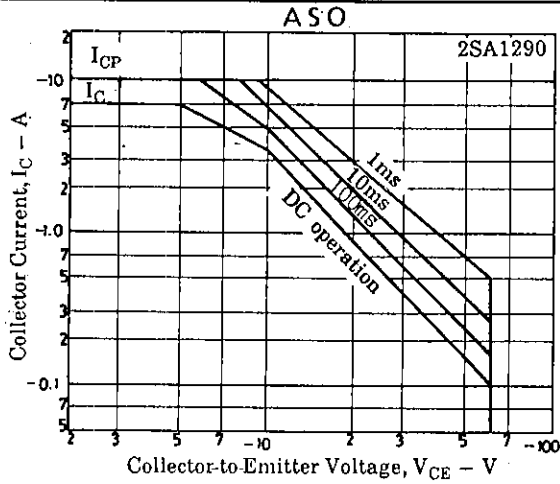
(unit : mm)



JEDEC : TO-220AB
EIAJ : SC-46

2SA1290/2SC3254





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